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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z4d
Core Size	32-Bit Dual-Core
Speed	120MHz
Connectivity	CANbus, LINbus, SCI, SPI, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	57
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 3.63V
Data Converters	A/D 32x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc56el60l3cbfqy

The eDMA module provides the following features:

- 16 channels supporting 8-, 16-, and 32-bit value single or block transfers
- Support variable sized queues and circular buffered queue
- Source and destination address registers independently configured to post-increment or stay constant
- Support major and minor loop offset
- Support minor and major loop done signals
- DMA task initiated either by hardware requestor or by software
- Each DMA task can optionally generate an interrupt at completion and retirement of the task
- Signal to indicate closure of last minor loop
- Transfer control descriptors mapped inside the SRAM

The eDMA controller is replicated for each processing channel.

1.5.5 On-chip flash memory with ECC

This device includes programmable, non-volatile flash memory. The non-volatile memory (NVM) can be used for instruction storage or data storage, or both. The flash memory module interfaces with the system bus through a dedicated flash memory array controller. It supports a 64-bit data bus width at the system bus port, and a 128-bit read data interface to flash memory. The module contains four 128-bit prefetch buffers. Prefetch buffer hits allow no-wait responses. Buffer misses incur a 3 wait state response at 120 MHz.

The flash memory module provides the following features

- 1 MB of flash memory in unique multi-partitioned hard macro
- Sectorization: 16 KB + 2 × 48 KB + 16 KB + 2 × 64 KB + 2 × 128 KB + 2 × 256 KB
- EEPROM emulation (in software) within same module but on different partition
- 16 KB test sector and 16 KB shadow block for test, censorship device and user option bits
- Wait states:
  - 3 wait states for frequencies =< 120 MHz
  - 2 wait states for frequencies =< 80 MHz
  - 1 wait state for frequencies =< 60 MHz
- Flash memory line 128-bit wide with 8-bit ECC on 64-bit word (total 144 bits)
- Accessed via a 64-bit wide bus for write and a 128-bit wide array for read operations
- 1-bit error correction, 2-bit error detection

1.5.6 On-chip SRAM with ECC

The SPC56ELx/SPC564Lx SRAM provides a general-purpose single port memory.

ECC handling is done on a 32-bit boundary for data and it is extended to the address to have the highest possible diagnostic coverage including the array internal address decoder.

1.5.33 Analog-to-Digital Converter module (ADC)

The ADC module features include:

Analog part:

- 2 on-chip ADCs
  - 12-bit resolution SAR architecture
  - Same digital interface as in the SPC560P family
  - A/D Channels: 9 external, 3 internal and 4 shared with other A/D (total 16 channels)
  - One channel dedicated to each T-sensor to enable temperature reading during application
  - Separated reference for each ADC
  - Shared analog supply voltage for both ADCs
  - One sample and hold unit per ADC
  - Adjustable sampling and conversion time

Digital part:

- 4 analog watchdogs comparing ADC results against predefined levels (low, high, range) before results are stored in the appropriate ADC result location
- 2 modes of operation: CPU Mode or CTU Mode
- CPU mode features
  - Register based interface with the CPU: one result register per channel
  - ADC state machine managing three request flows: regular command, hardware injected command, software injected command
  - Selectable priority between software and hardware injected commands
  - 4 analog watchdogs comparing ADC results against predefined levels (low, high, range)
  - DMA compatible interface
- CTU mode features
  - Triggered mode only
  - 4 independent result queues (1×16 entries, 2×8 entries, 1×4 entries)
  - Result alignment circuitry (left justified; right justified)
  - 32-bit read mode allows to have channel ID on one of the 16-bit parts
  - DMA compatible interfaces
- Built-in self-test features triggered by software

1.5.34 Cross Triggering Unit (CTU)

The ADC cross triggering unit allows automatic generation of ADC conversion requests on user selected conditions without CPU load during the PWM period and with minimized CPU load for dynamic configuration.

exceptions, etc.), allowing the development tool to interpolate what transpires between the discontinuities. Thus, static code may be traced.
  - Watchpoint messaging (WPM) via the auxiliary port
  - Watchpoint trigger enable of program and/or data trace messaging
  - Data tracing of instruction fetches via private opcodes

1.5.39 IEEE 1149.1 JTAG Controller (JTAGC)

The JTAGC block provides the means to test chip functionality and connectivity while remaining transparent to system logic when not in test mode. All data input to and output from the JTAGC block is communicated in serial format. The JTAGC block is compliant with the IEEE standard.

The JTAG controller provides the following features:

- IEEE Test Access Port (TAP) interface with 5 pins:
  - TDI
  - TMS
  - TCK
  - TDO
  - JCOMP
- Selectable modes of operation include JTAGC/debug or normal system operation
- 5-bit instruction register that supports the following IEEE 1149.1-2001 defined instructions:
  - BYPASS
  - IDCODE
  - EXTEST
  - SAMPLE
  - SAMPLE/PRELOAD
- 3 test data registers: a bypass register, a boundary scan register, and a device identification register. The size of the boundary scan register is parameterized to support a variety of boundary scan chain lengths.
- TAP controller state machine that controls the operation of the data registers, instruction register and associated circuitry

Table 4. LQFP144 pin function summary (continued)

Pin #	Port/function	Peripheral	Output function	Input function
95	$V_{DD\_HV\_REG\_1}$	—		
96	$V_{SS\_HV\_FLA}$	—		
97	$V_{DD\_HV\_FLA}$	—		
98	G[6]	SIUL	GPIO[102]	GPIO[102]
		FlexPWM_0	A[3]	A[3]
99	D[12]	SIUL	GPIO[60]	GPIO[60]
		FlexPWM_0	X[1]	X[1]
		LINFlexD_1	—	RXD
100	G[4]	SIUL	GPIO[100]	GPIO[100]
		FlexPWM_0	B[2]	B[2]
		eTimer_0	—	ETC[5]
101	C[13]	SIUL	GPIO[45]	GPIO[45]
		eTimer_1	ETC[1]	ETC[1]
		CTU_0	—	EXT_IN
		FlexPWM_0	—	EXT_SYNC
102	G[2]	SIUL	GPIO[98]	GPIO[98]
		FlexPWM_0	X[2]	X[2]
		DSPI_1	CS1	—
103	C[14]	SIUL	GPIO[46]	GPIO[46]
		eTimer_1	ETC[2]	ETC[2]
		CTU_0	EXT_TGR	—
104	G[3]	SIUL	GPIO[99]	GPIO[99]
		FlexPWM_0	A[2]	A[2]
		eTimer_0	—	ETC[4]
105	D[14]	SIUL	GPIO[62]	GPIO[62]
		FlexPWM_0	B[1]	B[1]
		eTimer_0	—	ETC[3]
106	F[12]	SIUL	GPIO[92]	GPIO[92]
		eTimer_1	ETC[3]	ETC[3]
		SIUL	—	EIRQ[30]
107	V_{PP_TEST}(1)	—		

Table 4. LQFP144 pin function summary (continued)

Pin #	Port/function	Peripheral	Output function	Input function
125	D[0]	SIUL	GPIO[48]	GPIO[48]
		FlexRay	CA_TX	—
		eTimer_1	ETC[1]	ETC[1]
		FlexPWM_0	B[1]	B[1]
126	$V_{DD\_HV\_IO}$	—		
127	$V_{SS\_HV\_IO}$	—		
128	D[3]	SIUL	GPIO[51]	GPIO[51]
		FlexRay	CB_TX	—
		eTimer_1	ETC[4]	ETC[4]
		FlexPWM_0	A[3]	A[3]
129	D[4]	SIUL	GPIO[52]	GPIO[52]
		FlexRay	CB_TR_EN	—
		eTimer_1	ETC[5]	ETC[5]
		FlexPWM_0	B[3]	B[3]
130	$V_{DD\_HV\_REG\_2}$	—		
131	$V_{DD\_LV\_COR}$	—		
132	$V_{SS\_LV\_COR}$	—		
133	F[0]	SIUL	GPIO[80]	GPIO[80]
		FlexPWM_0	A[1]	A[1]
		eTimer_0	—	ETC[2]
		SIUL	—	EIRQ[28]
134	A[9]	SIUL	GPIO[9]	GPIO[9]
		DSPI_2	CS1	—
		FlexPWM_0	B[3]	B[3]
		FlexPWM_0	—	FAULT[0]
135	$V_{DD\_LV\_COR}$	—		
136	A[13]	SIUL	GPIO[13]	GPIO[13]
		FlexPWM_0	B[2]	B[2]
		DSPI_2	—	SIN
		FlexPWM_0	—	FAULT[0]
		SIUL	—	EIRQ[12]
137	$V_{SS\_LV\_COR}$	—		

Table 5. LFBGA257 pin function summary (continued)

Pin #	Port/function	Peripheral	Output function	Input function
A5	H[0]	SIUL	GPIO[112]	GPIO[112]
		NPC	MDO[7]	—
A6	G[14]	SIUL	GPIO[110]	GPIO[110]
		NPC	MDO[9]	—
A7	D[3]	SIUL	GPIO[51]	GPIO[51]
		FlexRay	CB_TX	—
		eTimer_1	ETC[4]	ETC[4]
		FlexPWM_0	A[3]	A[3]
A8	C[15]	SIUL	GPIO[47]	GPIO[47]
		FlexRay	CA_TR_EN	—
		eTimer_1	ETC[0]	ETC[0]
		FlexPWM_0	A[1]	A[1]
		CTU_0	—	EXT_IN
		FlexPWM_0	—	EXT_SYNC
A9	$V_{DD\_HV\_IO\_RING}$	—		
A10	A[12]	SIUL	GPIO[12]	GPIO[12]
		DSPI_2	SOUT	—
		FlexPWM_0	A[2]	A[2]
		FlexPWM_0	B[2]	B[2]
		SIUL	—	EIRQ[11]
A11	H[10]	SIUL	GPIO[122]	GPIO[122]
		FlexPWM_1	X[2]	X[2]
		eTimer_2	ETC[2]	ETC[2]
A12	H[14]	SIUL	GPIO[126]	GPIO[126]
		FlexPWM_1	A[3]	A[3]
		eTimer_2	ETC[4]	ETC[4]
A13	A[10]	SIUL	GPIO[10]	GPIO[10]
		DSPI_2	CS0	CS0
		FlexPWM_0	B[0]	B[0]
		FlexPWM_0	X[2]	X[2]
		SIUL	—	EIRQ[9]
A14	B[2]	SIUL	GPIO[18]	GPIO[18]
		LINFlexD_0	TXD	—
		SSCM	DEBUG[2]	—
		SIUL	—	EIRQ[17]

Table 6. Supply pins (continued)

Supply		Pin #		
Symbol	**Description**	**100 pkg**	**144 pkg**	**257 pkg**
$V_{DD\_HV\_REG\_1}$	VDD_HV_REG_1	67	95	H15
$V_{SS\_HV\_FLA}$	VSS_HV_FLA	68	96	J16
$V_{DD\_HV\_FLA}$	VDD_HV_FLA	69	97	H16
$V_{DD\_HV\_IO}$	VDD_HV_IO	87	126	VDD_HV(3)
$V_{SS\_HV\_IO}$	VSS_HV_IO	88	127	VSS_HV(4)
$V_{DD\_HV\_REG\_2}$	VDD_HV_REG_2	91	130	C7
Power supply pins (1.2 V)				
$V_{SS\_LV\_COR}$	VSS_LV_COR Decoupling pins for core logic. Decoupling capacitor must be connected between these pins and the nearest $V_{DD\_LV\_COR}$ pin.	11	17	VSS_HV(2)
$V_{DD\_LV\_COR}$	VDD_LV_COR Decoupling pins for core logic. Decoupling capacitor must be connected between these pins and the nearest $V_{SS\_LV\_COR}$ pin.	12	18	VDD_LV(1)
V_{SS} 1V2	VSS_LV_PLL0_PLL1 / 1.2 V Decoupling pins for on-chip FMPLL modules. Decoupling capacitor must be connected between this pin and $V_{DD\_LV\_PLL}$.	24	35	N4
V_{DD} 1V2	VDD_LV_PLL0_PLL1 Decoupling pins for on-chip FMPLL modules. Decoupling capacitor must be connected between this pin and $V_{SS\_LV\_PLL}$.	25	36	P4
$V_{DD\_LV\_COR}$	VDD_LV_COR Decoupling pins for core logic. Decoupling capacitor must be connected between these pins and the nearest $V_{SS\_LV\_COR}$ pin.	28	39	VDD_LV(1)
$V_{SS\_LV\_COR}$	VSS_LV_COR Decoupling pins for core logic. Decoupling capacitor must be connected between these pins and the nearest $V_{DD\_LV\_COR}$ pin.	29	40	VSS_LV(2)
$V_{DD\_LV\_COR}$	VDD_LV_COR Decoupling pins for core logic and Regulator feedback. Decoupling capacitor must be connected between this pins and $V_{SS\_LV\_REGCOR}$.	—	70	VDD_LV(1)
$V_{SS\_LV\_COR}$	VSS_LV_REGCOR0 Decoupling pins for core logic and Regulator feedback. Decoupling capacitor must be connected between this pins and $V_{DD\_LV\_REGCOR}$.	—	71	VSS_LV(2)
$V_{DD\_LV\_COR}$	VDD_LV_COR Decoupling pins for core logic. Decoupling capacitor must be connected between these pins and the nearest $V_{SS\_LV\_COR}$ pin.	65	93	VDD_LV(1)
$V_{SS\_LV\_COR}$	VSS_LV_COR / 1.2 V Decoupling pins for core logic. Decoupling capacitor must be connected between these pins and the nearest $V_{DD\_LV\_COR}$ pin.	66	94	VSS_LV(2)
V_{DD} 1V2	VDD_LV_COR Decoupling pins for core logic. Decoupling capacitor must be connected between these pins and the nearest $V_{DD\_LV\_COR}$ pin.	92	131	VDD_LV(1)

Table 8. Pin muxing (continued)

Port name	PCR	Peripheral	Alternate output function	Output mux sel	Input functions	Input mux select	Weak pull config during reset	Pad speed(1)		Pin #		
								SRC = 1	SRC = 0	100 pkg	144 pkg	257 pkg
A[6]	PCR[6]	SIUL	GPIO[6]	ALT0	GPIO[6]	—	—	M	S	2	2	G4
		DSPI_1	SCK	ALT1	SCK	—						
		SIUL	—	—	EIRQ[6]	—						
A[7]	PCR[7]	SIUL	GPIO[7]	ALT0	GPIO[7]	—	—	M	S	4	10	F3
		DSPI_1	SOUT	ALT1	—	—						
		SIUL	—	—	EIRQ[7]	—						
A[8]	PCR[8]	SIUL	GPIO[8]	ALT0	GPIO[8]	—	—	M	S	6	12	F4
		DSPI_1	—	—	SIN	—						
		SIUL	—	—	EIRQ[8]	—						
A[9]	PCR[9]	SIUL	GPIO[9]	ALT0	GPIO[9]	—	—	M	S	94	134	B6
		DSPI_2	CS1	ALT1	—	—						
		FlexPWM_0	B[3]	ALT3	B[3]	PSMI[27]; PADSEL=1						
		FlexPWM_0	—	—	FAULT[0]	PSMI[16]; PADSEL=0						
A[10]	PCR[10]	SIUL	GPIO[10]	ALT0	GPIO[10]	—	—	M	S	81	118	A13
		DSPI_2	CS0	ALT1	CS0	PSMI[3]; PADSEL=1						
		FlexPWM_0	B[0]	ALT2	B[0]	PSMI[24]; PADSEL=0						
		FlexPWM_0	X[2]	ALT3	X[2]	PSMI[29]; PADSEL=0						
		SIUL	—	—	EIRQ[9]	—						

Table 8. Pin muxing (continued)

Port name	PCR	Peripheral	Alternate output function	Output mux sel	Input functions	Input mux select	Weak pull config during reset	Pad speed(1)		Pin #		
								SRC = 1	SRC = 0	100 pkg	144 pkg	257 pkg
B[6]	PCR[22]	SIUL	GPIO[22]	ALT0	GPIO[22]	—	—	F	S	96	138	B3
		MC_CGM	clk_out	ALT1	—	—						
		DSPI_2	CS2	ALT2	—	—						
		SIUL	—		EIRQ[18]	—						
B[7]	PCR[23]	SIUL	—	ALT0	GPI[23]	—	—	—	—	30	43	R5
		LINFlexD_0	—	—	RXD	PSMI[31]; PADSEL=1						
		ADC_0	—	—	AN[0](3)	—						
B[8]	PCR[24]	SIUL	—	ALT0	GPI[24]	—	—	—	—	31	47	P7
		eTimer_0	—	—	ETC[5]	PSMI[8]; PADSEL=2						
		ADC_0	—	—	AN[1](3)	—						
B[9]	PCR[25]	SIUL	—	ALT0	GPI[25]	—	—	—	—	35	52	U7
		ADC_0 ADC_1	—	—	AN[11](3)	—						
B[10]	PCR[26]	SIUL	—	ALT0	GPI[26]	—	—	—	—	36	53	R8
		ADC_0 ADC_1	—	—	AN[12](3)	—						
B[11]	PCR[27]	SIUL	—	ALT0	GPI[27]	—	—	—	—	37	54	T8
		ADC_0 ADC_1	—	—	AN[13](3)	—						
B[12]	PCR[28]	SIUL	—	ALT0	GPI[28]	—	—	—	—	38	55	U8
		ADC_0 ADC_1	—	—	AN[14](3)	—						

3 Electrical characteristics

3.1 Introduction

This section contains detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications for this device.

This device is designed to operate at 120 MHz. The electrical specifications are preliminary and are from previous designs, design simulations, or initial evaluation. These specifications may not be fully tested or guaranteed at this early stage of the product life cycle. Finalized specifications will be published after complete characterization and device qualifications have been completed.

The “Symbol” column of the electrical parameter and timings tables contains an additional column containing “SR”, “CC”, “P”, “C”, “T”, or “D”.

- “SR” identifies system requirements—conditions that must be provided to ensure normal device operation. An example is the input voltage of a voltage regulator.
- “CC” identifies controller characteristics—indicating the characteristics and timing of the signals that the chip provides.
- “P”, “C”, “T”, or “D” apply only to controller characteristics—specifications that define normal device operation. They specify how each characteristic is guaranteed.
  - P: parameter is guaranteed by production testing of each individual device.
  - C: parameter is guaranteed by design characterization. Measurements are taken from a statistically relevant sample size across process variations.
  - T: parameter is guaranteed by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values are shown in the typical (“typ”) column are within this category.
  - D: parameters are derived mainly from simulations.

3.2 Absolute maximum ratings

Table 9. Absolute maximum ratings(1)

Symbol		Parameter	Conditions	Min	Max	Unit
$V_{DD\_HV\_REG}$	SR	3.3 V voltage regulator supply voltage	—	–0.3	4.5(2), (3)	V
$V_{DD\_HV\_IOx}$	SR	3.3 V input/output supply voltage	—	–0.3	4.5 (2), (3)	V
$V_{SS\_HV\_IOx}$	SR	Input/output ground voltage	—	–0.1	0.1	V
$V_{DD\_HV\_FLA}$	SR	3.3 V flash supply voltage	—	–0.3	4.5 (2), (3)	V
$V_{SS\_HV\_FLA}$	SR	Flash memory ground	—	–0.1	0.1	V
$V_{DD\_HV\_OSC}$	SR	3.3 V crystal oscillator amplifier supply voltage	—	–0.3	4.5 (2), (3)	V
$V_{SS\_HV\_OSC}$	SR	3.3 V crystal oscillator amplifier reference voltage	—	–0.1	0.1	V
$V_{DD\_HV\_ADR0}$ (2)(3) $V_{DD\_HV\_ADR1}$	SR	3.3 V / 5.0 V ADC_0 high reference voltage 3.3 V / 5.0 V ADC_1 high reference voltage	—	–0.3	6.4 (2)	V

Table 14. Thermal characteristics for LFBGA257 package(1)

Symbol		Parameter	Conditions	Value	Unit
$R_{\theta JA}$	D	Thermal resistance junction-to-ambient natural convection(2)	Single layer board – 1s	46	°C/W
			Four layer board – 2s2p	26	
$R_{\theta JMA}$	D	Thermal resistance, junction-to-ambient forced convection at 200 ft/min	Single layer board – 1s	37	°C/W
			Four layer board – 2s2p	22	
$R_{\theta JB}$	D	Thermal resistance junction-to-board(3)	—	13	°C/W
$R_{\theta JC}$	D	Thermal resistance junction-to-case(4)	—	8	°C/W
Ψ_{JT}	D	Junction-to-package-top natural convection(5)	—	2	°C/W

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Junction-to-Ambient thermal resistance determined per JEDEC JESD51-3 and JESD51-6. Thermal test board meets JEDEC specification for this package.
3. Junction-to-Board thermal resistance determined per JEDEC JESD51-8. Thermal test board meets JEDEC specification for the specified package.
4. Junction-to-Case at the top of the package determined using MIL-STD 883 Method 1012.1. The cold plate temperature is used for the case temperature. Reported value includes the thermal resistance of the interface layer.
5. Thermal characterization parameter indicating the temperature difference between the package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

3.5.1 General notes for specifications at maximum junction temperature

An estimation of the chip junction temperature, T_J, can be obtained from *Equation 1*:

Equation 1: $T_J = T_A + (R_{\theta JA} \times P_D)$

where:

T_A= ambient temperature for the package (^oC)

$R_{\theta JA}$= junction to ambient thermal resistance ($^oC/W$)

P_D= power dissipation in the package (W)

The junction to ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. Unfortunately, there are two values in common usage: the value determined on a single layer board and the value obtained on a board with two planes. For packages such as the PBGA, these values can be different by a factor of two. Which value is closer to the application depends on the power dissipated by other components on the board. The value obtained on a single layer board is appropriate for the tightly packed printed circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated.

When a heat sink is used, the thermal resistance is expressed in *Equation 2* as the sum of a junction to case thermal resistance and a case to ambient thermal resistance:

EME testing was performed and documented according to these standards: [IEC 61967-2 & -4]

EMS testing was performed and documented according to these standards: [IEC 62132-2 & -4]

Refer SPC56EL60 for detailed information pertaining to the EMC, EME, and EMS testing and results.

3.7 Electrostatic discharge (ESD) characteristics

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (*n* + 1) supply pin). This test conforms to the AEC-Q100-002/-003/-011 standard. For more details, refer to the application note *Electrostatic Discharge Sensitivity Measurement* (AN1181).

SPC56XL60/54 makes a transition from HPREG1 to HPREG2. This transition is dynamic. Once HPREG2 is fully operational, the controller part of HPREG1 is switched off.

The following bipolar transistors are supported:

- BCP68 from ON Semiconductor
- BCX68 from Infineon

Table 19. Characteristics

Symbol	Parameter	Value	Unit
$h_{FE}(\beta)$	DC current gain (Beta)	85 - 375	—
P_D	Maximum power dissipation @ T_A=25°C(1)	1.5	W
I_{CMaxDC}	Maximum peak collector current	1.0	A
VCE_{SAT}	Collector-to-emitter saturation voltage (Max)	600(2)	mV
V_{BE}	Base-to-emitter voltage (Max)	1.0	V

1. Derating factor 12mW/degC.
2. Adjust resistor at bipolar transistor collector for 3.3V to avoid VCE<VCE_{SAT}.

The recommended external ballast transistor is the bipolar transistor BCP68 with the gain range of 85 up to 375 (for IC=500mA, VCE=1V) provided by several suppliers. This includes the gain variations BCP68-10, BCP68-16 and BCP68-25.The most important parameters for the interoperability with the integrated voltage regulator are the DC current gain (hFE) and the temperature coefficient of the gain (XTB). While the specified gain range of most BCP68 vendors is the same, there are slight variations in the temperature coefficient parameter. SPC56XL60/54 Voltage regulator operation was simulated against the typical variation on temperature coefficient and against the specified gain range to have a robust design.

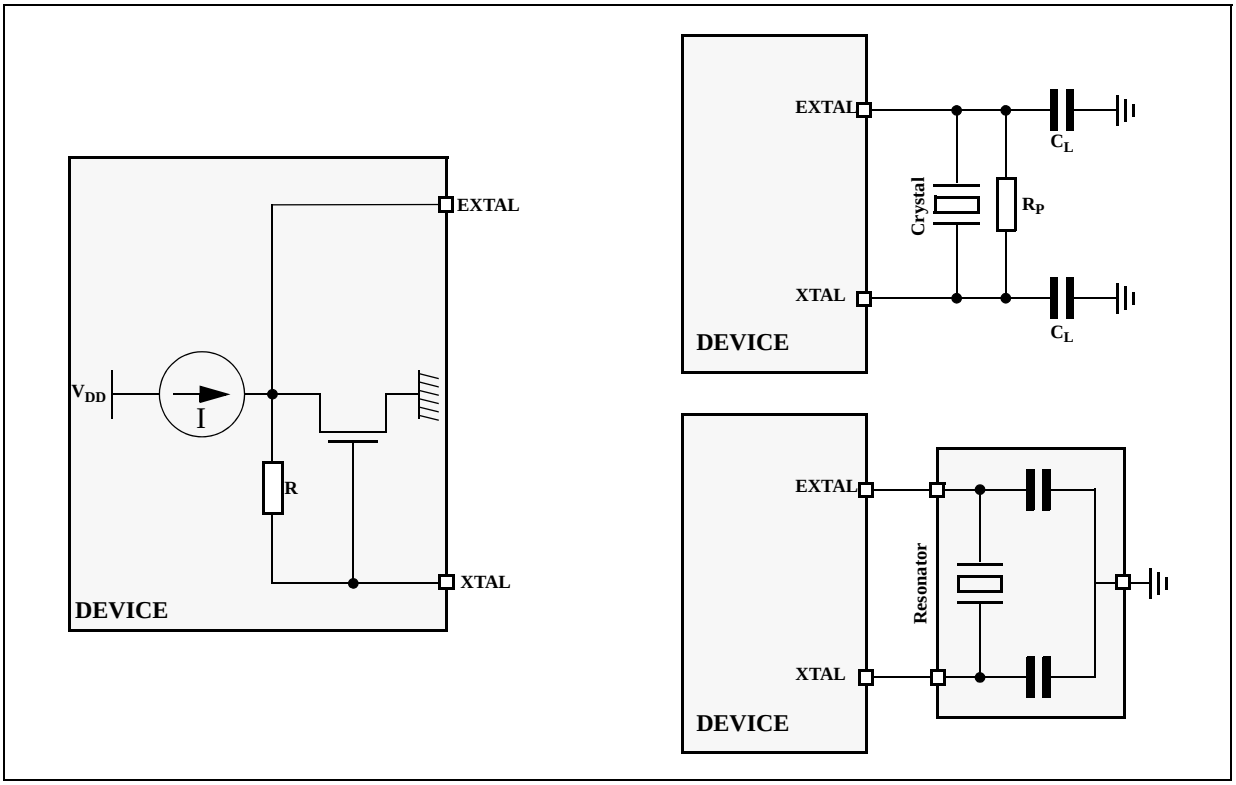
Table 20. Voltage regulator electrical specifications

Symbol		Parameter	Conditions	Min	Typ	Max	Unit
C_{ext}		External decoupling/ stability capacitor	Min, max values shall be granted with respect to tolerance, voltage, temperature, and aging variations.	12	—	40	µF
	SR	Combined ESR of external capacitor	—	1	—	100	mΩ
	SR	Number of pins for external decoupling/ stability capacitor	—	5	—	—	—
C_{V1V2}	SR	Total capacitance on 1.2 V pins	Ceramic capacitors, taking into account tolerance, aging, voltage and temperature variation	300	—	900	nF
t_{SU}		Start-up time after main supply stabilization	C_{load} = 10 µF × 4	—	—	2.5	ms

3.13 Main oscillator electrical characteristics

The device provides an oscillator/resonator driver. *Figure 7* describes a simple model of the internal oscillator driver and provides an example of a connection for an oscillator or a resonator.

Figure 7. Crystal oscillator and resonator connection scheme



Note: XTAL/EXTAL must not be directly used to drive external circuits.

Figure 8. Main oscillator electrical characteristics

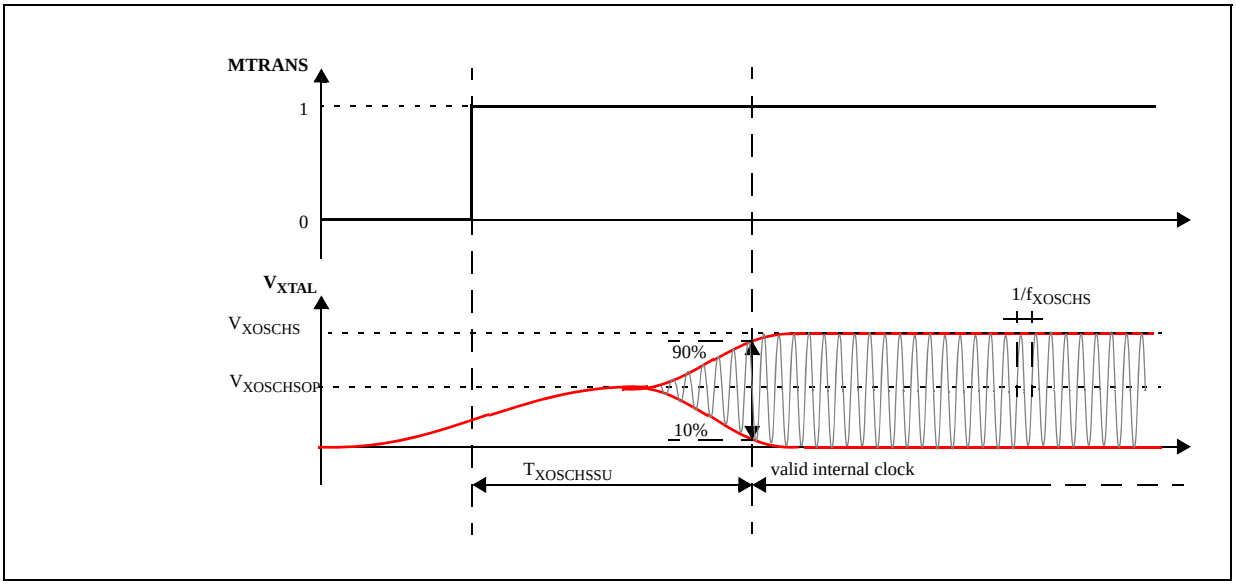
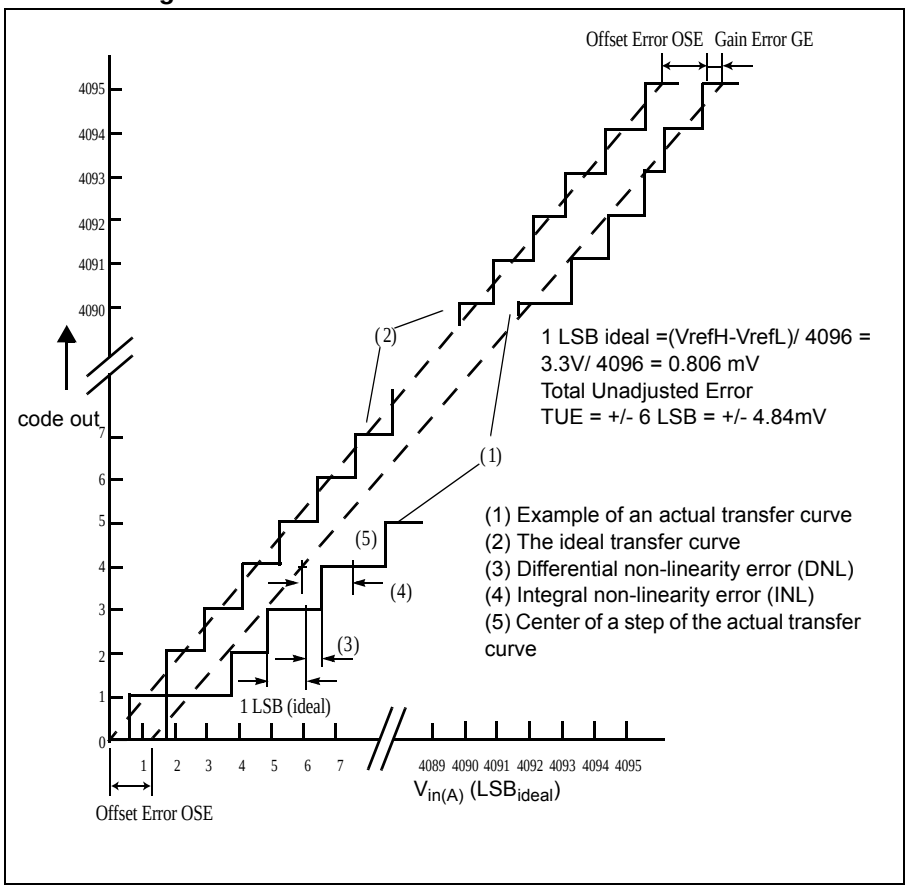


Table 24. Main oscillator electrical characteristics

Symbol		Parameter	Conditions[1]	Value			Unit
				Min	Typ	Max	
f_{XOSCHS}	SR	Oscillator frequency	—	4.0	—	40.0	MHz
$g_{mXOSCHS}$	P	Oscillator transconductance	V_{DD} = 3.3 V ±10%	4.5	—	13.25	mA/V
V_{XOSCHS}	D	Oscillation amplitude	f_{OSC} = 4, 8, 10, 12, 16 MHz	1.3	—	—	V
			f_{OSC} = 40 MHz	1.1	—	—	
$V_{XOSCHSOP}$	D	Oscillation operating point	—	—	0.82	—	V
$T_{XOSCHSSU}$	T	Oscillator start-up time	f_{OSC} = 4, 8, 10, 12 MHz[2]	—	—	6	ms
			f_{OSC} = 16, 40 MHz[2]	—	—	2	
V_{IH}	SR	Input high level CMOS Schmitt Trigger	Oscillator bypass mode	0.65 × V_{DD}	—	V_{DD} + 0.4	V
V_{IL}	SR	Input low level CMOS Schmitt Trigger	Oscillator bypass mode	–0.4	—	0.35 × V_{DD}	V

1. V_{DD} = 3.3 V ±10%, T_J = –40 to +150 °C, unless otherwise specified.
2. The recommended configuration for maximizing the oscillator margin are:
   XOSC_MARGIN = 0 for 4 MHz quartz
   XOSC_MARGIN = 1 for 8/16/40 MHz quartz

Figure 9. ADC characteristics and error definitions



3.16.1 Input Impedance and ADC Accuracy

To preserve the accuracy of the A/D converter, it is necessary that analog input pins have low AC impedance. Placing a capacitor with good high frequency characteristics at the input pin of the device can be effective: the capacitor should be as large as possible, ideally infinite. This capacitor contributes to attenuating the noise present on the input pin; further, it sources charge during the sampling phase, when the analog signal source is a high-impedance source.

A real filter can typically be obtained by using a series resistance with a capacitor on the input pin (simple RC filter). The RC filtering may be limited according to the value of source impedance of the transducer or circuit supplying the analog signal to be measured. The filter at the input pins must be designed taking into account the dynamic characteristics of the input signal (bandwidth) and the equivalent input impedance of the ADC itself.

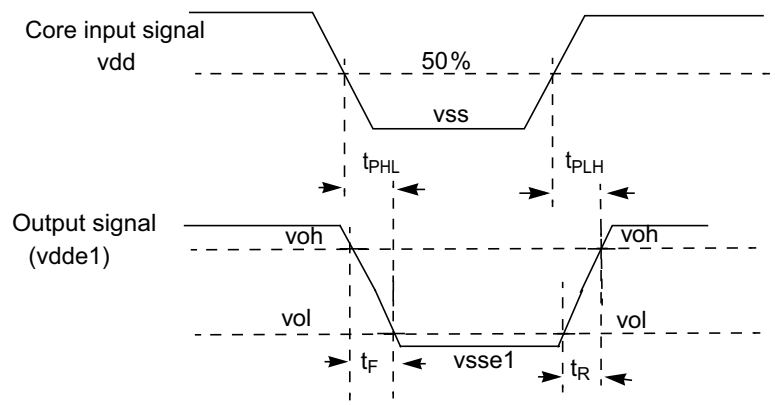
In fact a current sink contributor is represented by the charge sharing effects with the sampling capacitance: C_S and C_{p2} being substantially a switched capacitance, with a frequency equal to the conversion rate of the ADC, it can be seen as a resistive path to ground. For instance, assuming a conversion rate of 1 MHz, with C_{p2} + CS equal to 7.5 pF, a resistance of 133 kΩ is obtained (R_{EQ} = 1 / (fS*(C_{p2}+C_S)), where fS represents the conversion rate at the considered channel). To minimize the error induced by the voltage partitioning between this resistance (sampled voltage on C_s) and the sum of R_S + R_F, the external circuit must be designed to respect the *Equation 4*:

Table 32. Pad AC specifications (3.3 V, IPP_HVE = 0)(1) (continued)

No.	Pad		Tswitchon(1)(ns)			Rise/Fall(2) (ns)			Frequency (MHz)			Current slew(3) (mA/ns)			Load drive (pF)
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
3	Fast	T	1	—	6	—	—	4	—	—	72	3	—	40	25
			1	—	6	—	—	7	—	—	55	7	—	40	50
			1	—	6	—	—	12	—	—	40	7	—	40	100
			1	—	6	—	—	18	—	—	25	7	—	40	200
4	Symmetric	T	1	—	8	—	—	5	—	—	50	3	—	25	25

1. Propagation delay from $V_{DD\_HV\_IOx}/2$ of internal signal to Pchannel/Nchannel switch-on condition (i.e. t_PHL and t_PLH in *Figure 13: Pad output delay*).
2. Slope at rising/falling edge (i.e. t_F and t_R in *Figure 13: Pad output delay*).
3. Data based on characterization results, not tested in production.

Figure 13. Pad output delay



[1] t_F and t_R are transient times at the FAR END.
[2] t_{PHL} and t_{PLH} are measured at the pad.
[3] Core input slew = 1ns (0 to vdd).

3.20 Reset sequence

This section shows the duration for different reset sequences. It describes the different reset sequences and it specifies the start conditions and the end indication for the reset sequences.

3.20.1 Reset sequence duration

Table 33 specifies the minimum and the maximum reset sequence duration for the five different reset sequences described in *Section 3.20.2*.

Figure 15. Destructive Reset Sequence, BIST disabled

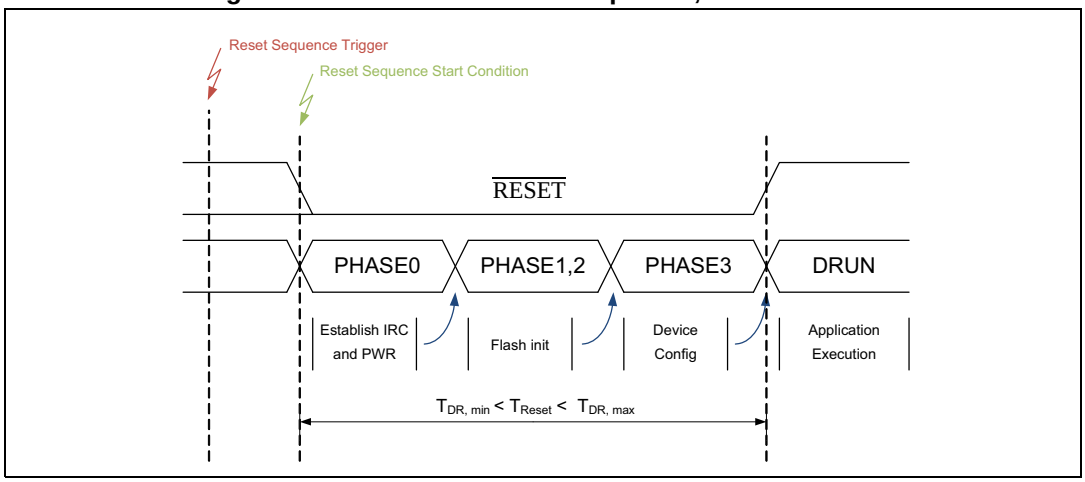


Figure 16. External Reset Sequence Long, BIST enabled

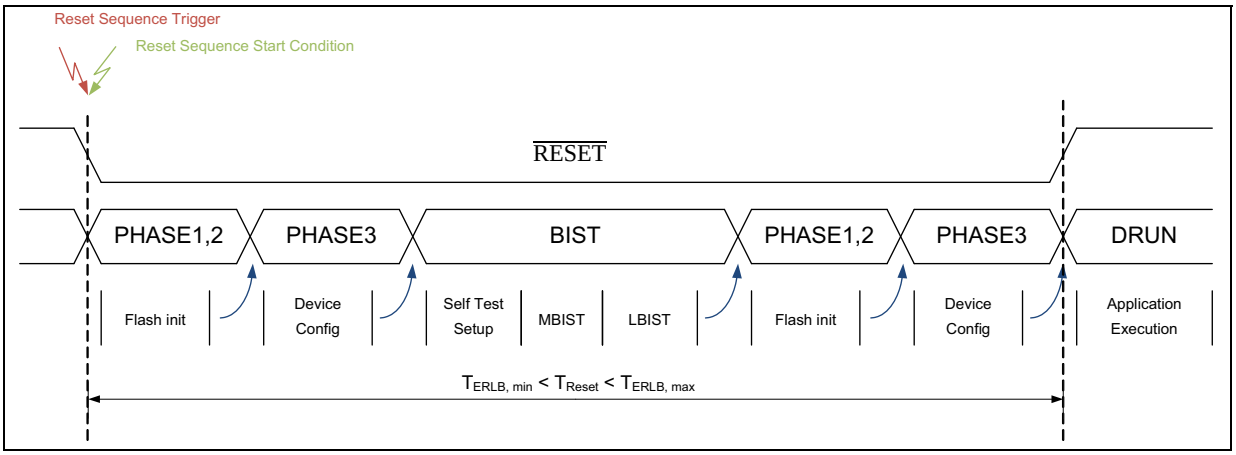


Figure 17. Functional Reset Sequence Long

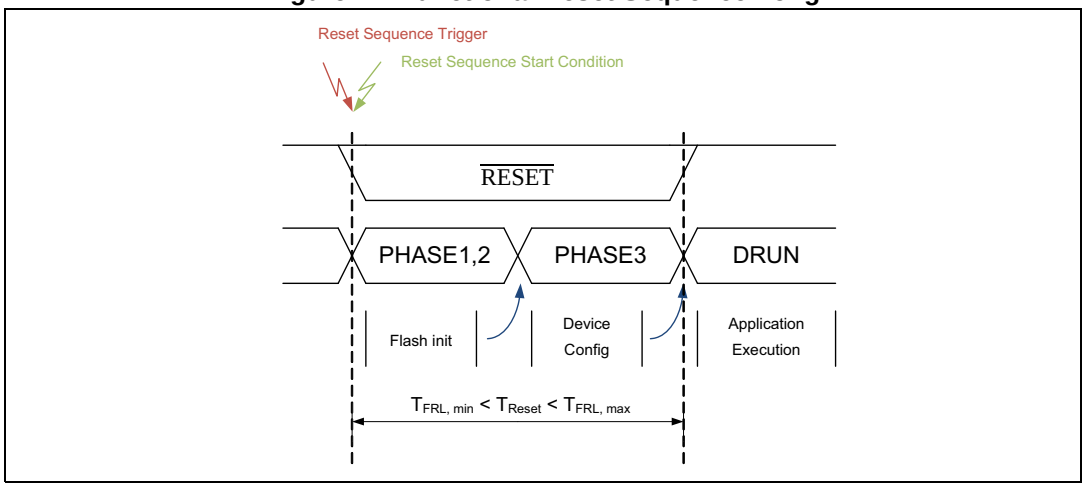


Figure 19. Reset sequence start for Destructive Resets

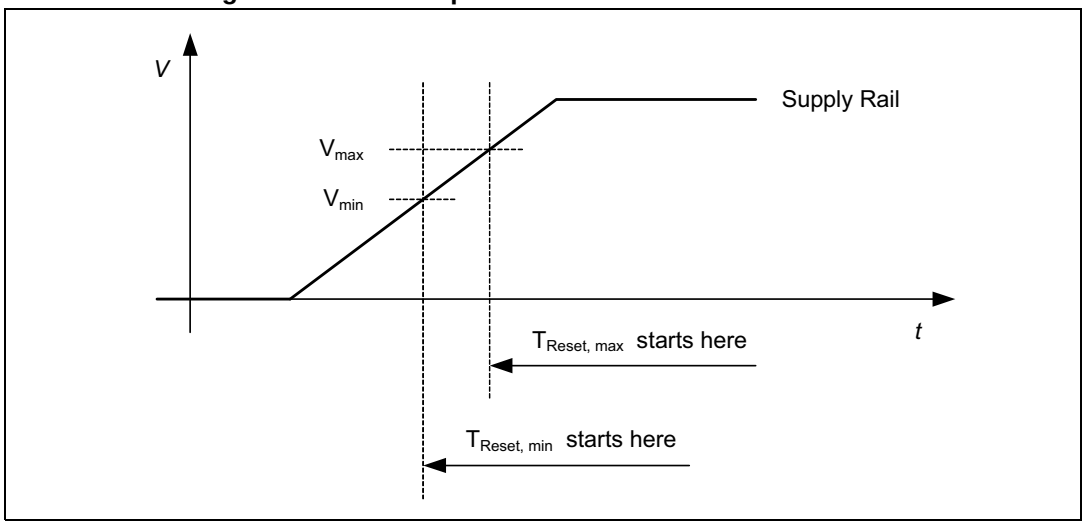


Table 35. Voltage Thresholds

Variable name	Value
V_{min}	Refer to *Table 20*
V_{max}	Refer to *Table 20*
Supply Rail	VDD_HV_PMU

3.20.4.2 External reset via $\overline{\text{RESET}}$

Figure 20 shows the voltage thresholds that determine the start of the reset sequences initiated by the assertion of $\overline{\text{RESET}}$ as specified in *Table 34*.

Figure 20. Reset sequence start via $\overline{\text{RESET}}$ assertion

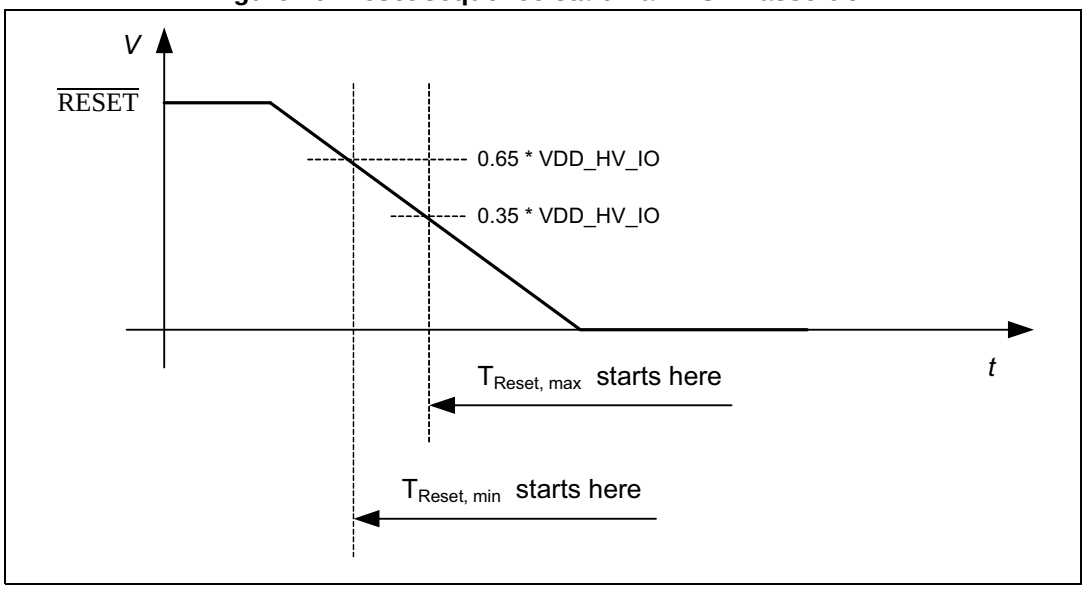


Table 45. Document revision history

Date	Revision	Changes
14-Jun-2010	4 (continued)	In the “Main oscillator electrical characteristics” table, changed the maximum specification for $g_{mXOSCHS}$ (was 11 mA/V, is 11.8 mA/V). Revised the “ADC electrical characteristics” section.In the “ADC conversion characteristics” table: – Changed the t_{ADC_S} specification (was TBD, is minimum of 383 ns). – Added the footnote “No missing codes” to the DNL specification. – Added specifications for SNR, THD, SINAD, and ENOB. Revised the “Ordering information” section.
23-Nov-2010	5	Editorial changes and improvements. Revised the Overview section. Replaced references to PowerPC with references to Power Architecture. In the feature summary, changed “As much as 128 KB on-chip SRAM” to “128 KB on-chip SRAM”. In the “Feature details” section: – In the “On-chip SRAM with ECC” section, added information about required RAM wait states. – In the PIT section, deleted “32-bit counter for real time interrupt, clocked from main external oscillator” (not supported on this device). – In the flash-memory section, changed “16 KB Test” to “16 KB test sector”, revised the wait state information, and deleted the associated Review_Q&A content. – In the SRAM section, revised the wait state information. In the 100-pin pinout diagram: – Renamed pin 41 (was VDD_HV_ADV0_ADV1, is VDD_HV_ADV). – Renamed pin 42 (was VSS_HV_ADV0_ADV1, is VSS_HV_ADV). In the 144-pin pinout diagram: – Renamed pin 58 (was VDD_HV_ADV0_ADV1, is VDD_HV_ADV). – Renamed pin 59 (was VSS_HV_ADV0_ADV1, is VSS_HV_ADV). Added the “LQFP100 pin function summary” table. In the “LQFP144 pin function summary” table, for pin 39, changed $V_{SS\_LV\_COR}$ to $V_{DD\_LV\_COR}$. In the “Supply pins” table: – Changed the description for $V_{DD\_LV\_COR}$ (was “Voltage regulator supply voltage”, is “Core logic supply”). – Changed the description for $V_{DD\_HV\_PMU}$ (was “Core regulator supply”, is “Voltage regulator supply”). In the “Pin muxing” table: – In the “Pad speed” column headings, changed “SRC = 0” to “SRC = 1” and “SRC = 1” to “SRC = 0” – For port B[6], changed the pad speed for SRC=0 (was M, is F). In the “Thermal characteristics” section, added meaningful values to the thermal-characteristics tables. Added the “SWG electrical specifications” section. In the “Voltage regulator electrical characteristics” section, changed the table title (was “HPREG1, HPREG2, Main LVDs, Digital HVD, and Digital LVD electrical specifications”, is “Voltage regulator electrical characteristics”) and revised the table.